

ABSTRACT OF THE DISCLOSURE

A semiconductor device having a capacitor formed in a multilayer wiring structure, the semiconductor device comprising a multilayer wiring structure including a plurality of wiring layers formed on a substrate, a capacitor arranged in a predetermined wiring layer in the multilayer wiring structure and having a lower electrode, a dielectric film, and an upper electrode, a first via formed in the predetermined wiring layer and connected to a top surface of the upper electrode of the capacitor, and a second via formed in an overlying wiring layer stacked on the predetermined wiring layer, the second via being formed on the first via.